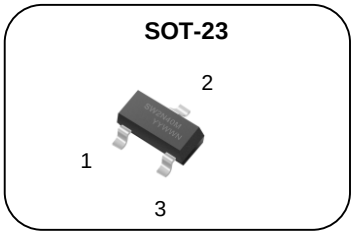
N-channel Enhanced mode SOT-23 MOSFET

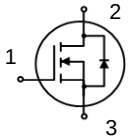
Features

- High ruggedness
- Low $R_{DS(ON)}$ (Typ 9.0Ω)@V_{GS}=10V
- Low Gate Charge (Typ 2.8nC)
- Improved dv/dt Capability
- Application: High frequency switching mode power supply,Electronic ballast,UPS,PFC, High power switching power supply, Control of electric welding machine



1. Gate 2. Drain 3. Source

BV_{DSS} : 400V
I_D : 1A
$R_{DS(ON)}$: 9.0Ω



LEAD-FREE RoHS

General Description

This power MOSFET is produced with advanced technology of SAMWIN.
This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW E 2N40M	SW2N40M	SOT-23	REEL

Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to source voltage	400	V
I_D	Continuous drain current (@T_a=25°C)	1*	A
	Continuous drain current (@T_a=100°C)	0.63*	A
I_{DM}	Drain current pulsed (note 1)	4	A
V_{GS}	Gate to source voltage	±30	V
dv/dt	Peak diode recovery dv/dt (note 3)	5	V/ns
P_D	Total power dissipation (@T_a=25°C)	1.3	W
	Derating factor above 25°C	0.01	W/°C
T_{STG}, T_J	Operating junction temperature & storage temperature	-55 ~ + 150	°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value	Unit
R_{thja}	Thermal resistance, Junction to ambient	98	°C/W

Note: R_{thja} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{thjc} is guaranteed by design while R_{thca} is determined by the user's board design.

SO-T23 R_{thja} : 98°C/W on a 1 in^2 pad of 2oz copper.

Electrical characteristic (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	400			V
ΔBV_{DSS} / ΔT_J	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25°C		0.23		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=400V, V_{GS}=0V			1	uA
		V_{DS}=320V, T_J=125°C			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=30V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-30V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	2.2		4.0	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D=0.1A,T_J=25°C		9.0	14	Ω
		V_{GS}=10V, I_D=0.1A,T_J=125°C		12.6		Ω
G_{fs}	Forward transconductance	V_{DS}=30V, I_D=0.5A		0.53		S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz		71		pF
C_{oss}	Output capacitance			21		
C_{rss}	Reverse transfer capacitance			1.1		
$t_{d(on)}$	Turn on delay time	V_{DS}=200V, I_D=1A, R_G=10Ω, V_{GS}=10V (note 4,5)		3.3		ns
t_r	Rising time			9		
$t_{d(off)}$	Turn off delay time			5.6		
t_f	Fall time			13		
Q_g	Total gate charge	V_{DS}=320V, V_{GS}=10V, I_D=1A , I_G=0.1mA (note 4,5)		2.8		nC
Q_{gs}	Gate-source charge			0.7		
Q_{gd}	Gate-drain charge			0.2		
R_g	Gate resistance	V_{DS}=0V, Scan F mode		26		Ω

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			1	A
I_{SM}	Pulsed source current				4	A
V_{SD}	Diode forward voltage drop.	I_S=0.2A, V_{GS}=0V			1.4	V
t_{rr}	Reverse recovery time	I_S=1A, V_{GS}=0V, dI_F/dt=100A/us		155		ns
Q_{rr}	Reverse recovery charge			265		nC

※. Notes

1. Repeatitive rating : pulse width limited by junction temperature.
2. I_{SD} ≤1A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
3. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

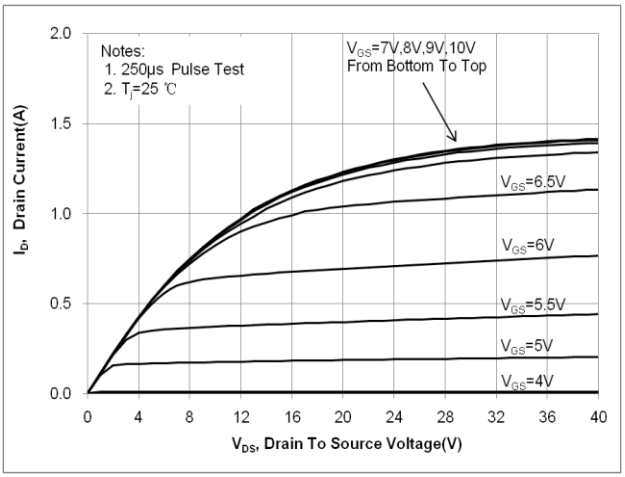


Fig. 2. Transfer Characteristics

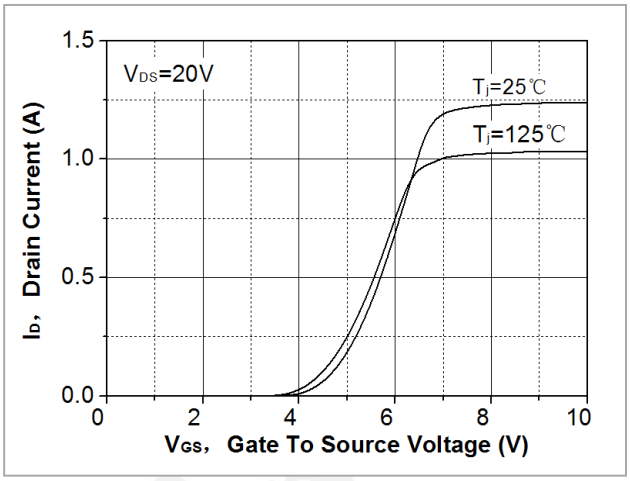


Fig. 3. On-resistance variation vs. drain current and gate voltage

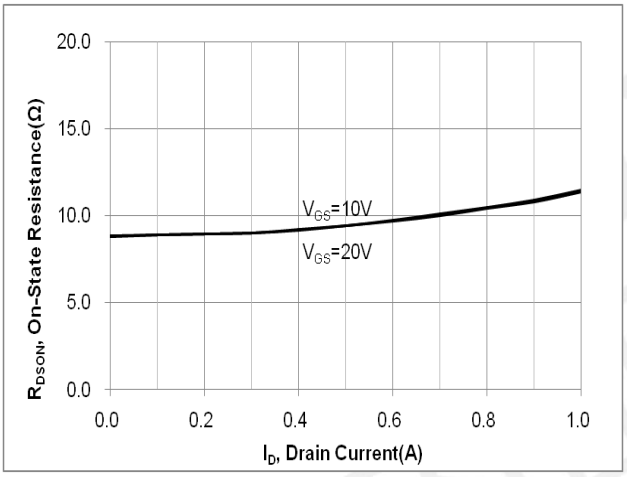


Fig. 4. On-state current vs. diode forward voltage

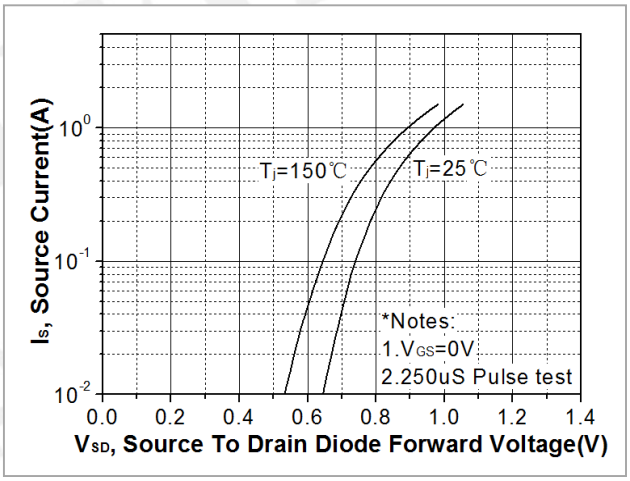


Fig 5. Breakdown voltage variation vs. junction temperature

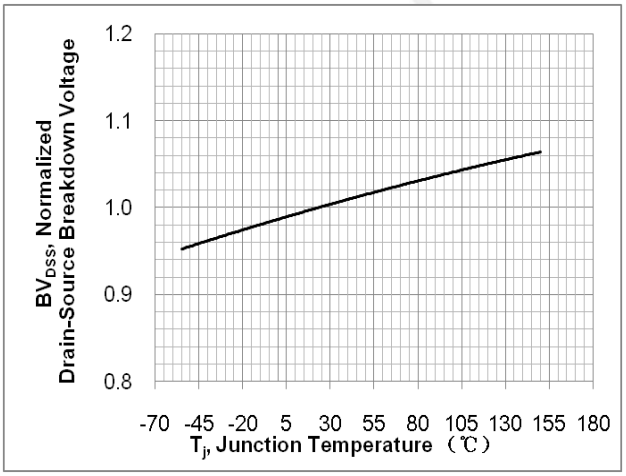


Fig. 6. On-resistance variation vs. junction temperature

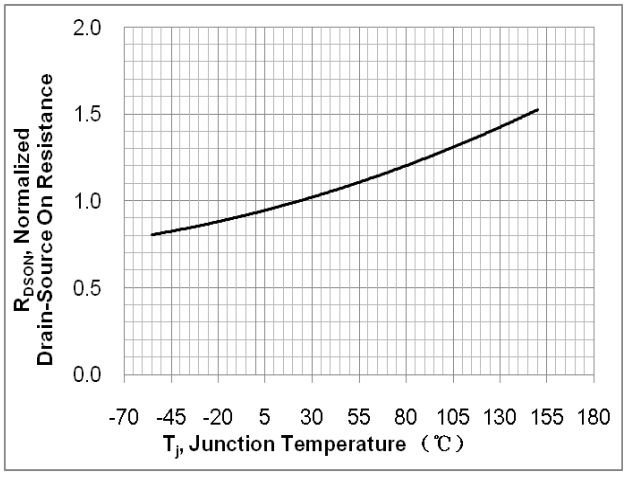


Fig. 7. Gate charge characteristics

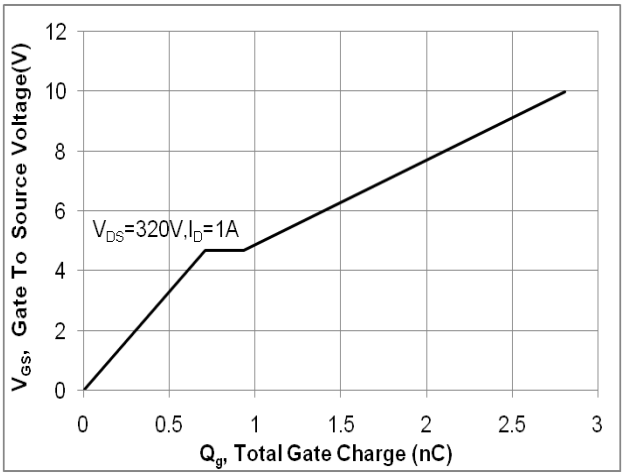


Fig. 8. Capacitance Characteristics

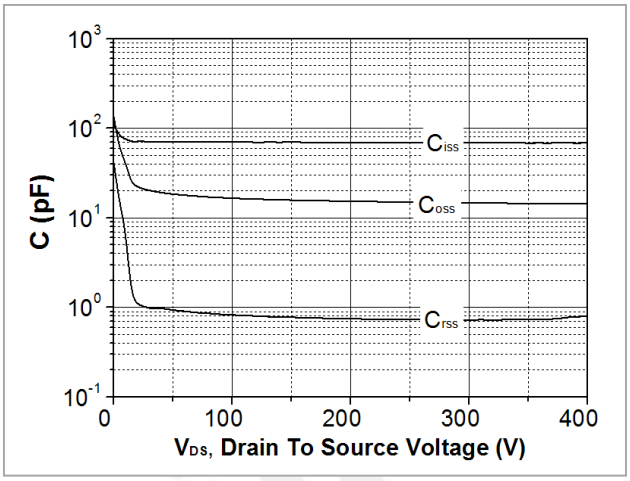


Fig. 9. Maximum safe operating area

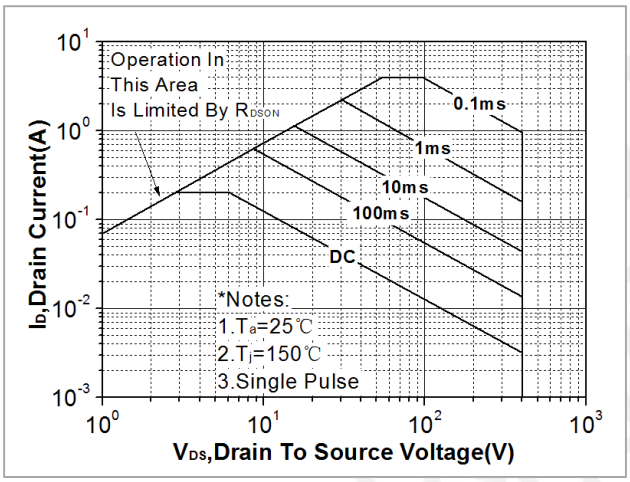


Fig. 10. Transient thermal response curve

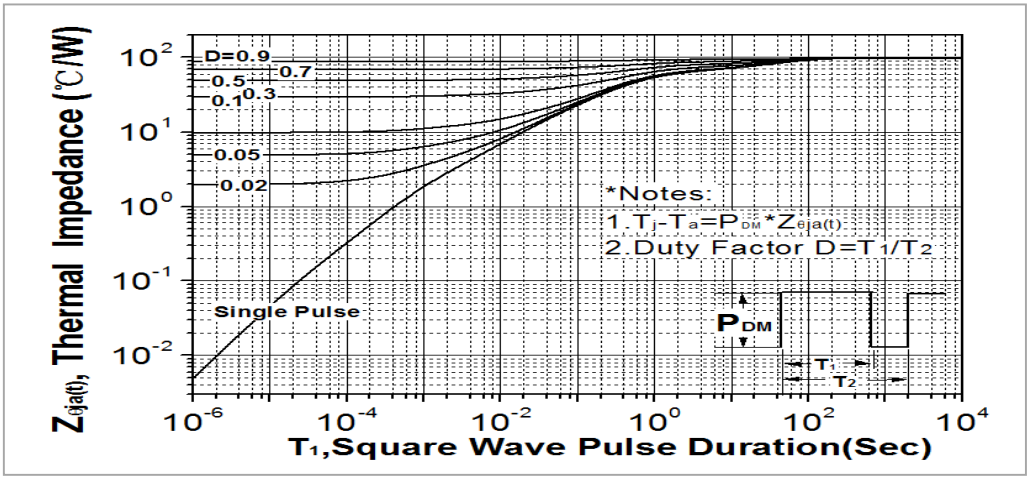


Fig. 11. Gate charge test circuit & waveform

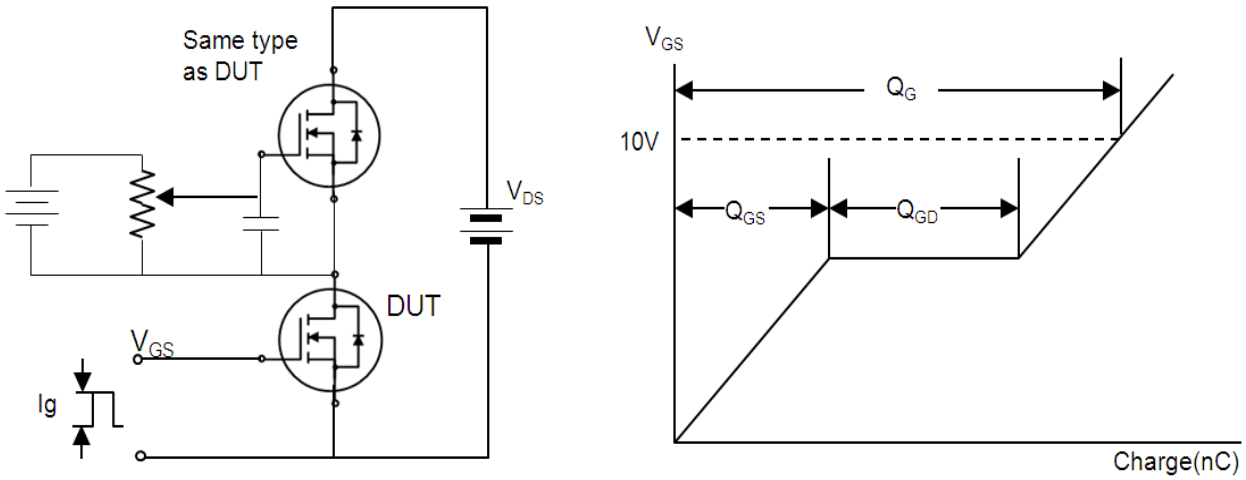


Fig. 12. Switching time test circuit & waveform

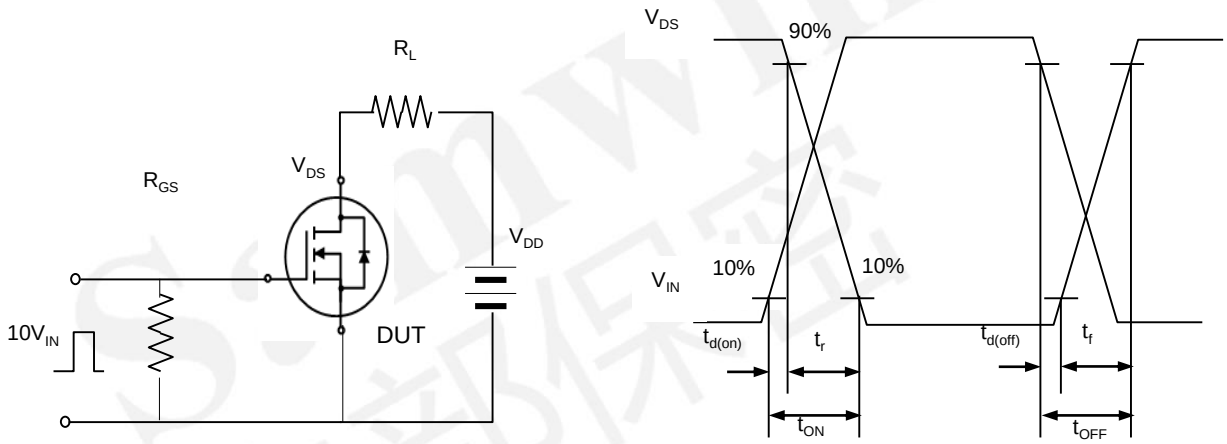
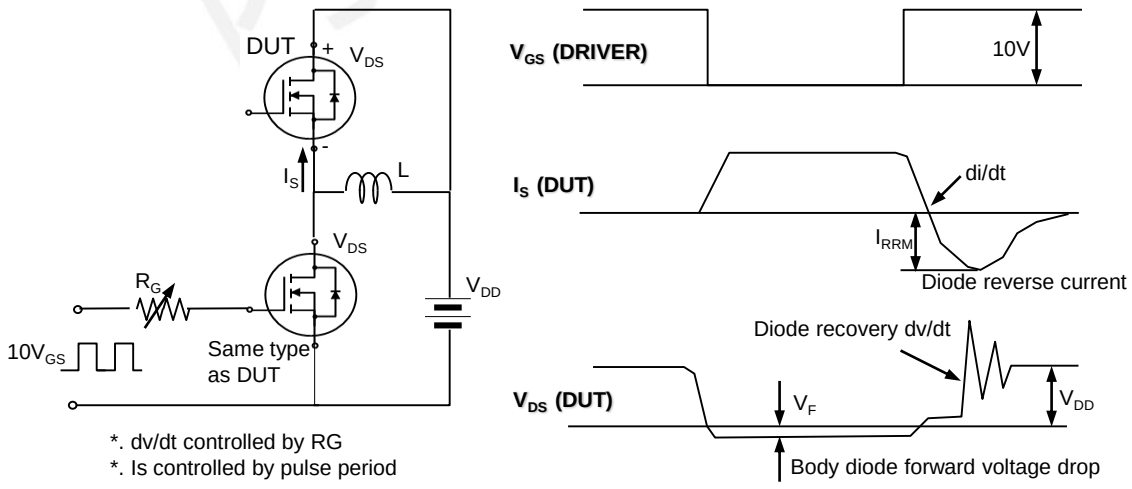


Fig. 13. Peak diode recovery dv/dt test circuit & waveform



*. dv/dt controlled by RG
*. Is controlled by pulse period

DISCLAIMER

* All the data & curve in this document was tested in SEMIPOWER TESTING & APPLICATION CENTER.
* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
* Qualification standards can also be found on the Web site (**http://www.semipower.com.cn**)
* Suggestions for improvement are appreciated, Please send your suggestions to **samwin@samwinsemi.com**